

APT5085BN	500V	9.5A	0.85Ω
APT4585BN	450V	9.5A	0.85Ω
APT501R1BN	500V	9.0A	1.10Ω
APT451R1BN	450V	9.0A	1.10Ω

POWER MOS IV®

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT				UNIT
		4585BN	5085BN	451R1BN	501R1BN	
V _{DSS}	Drain-Source Voltage	450	500	450	500	Volts
I _D	Continuous Drain Current	9.5		9.0		Amps
I _{DM}	Pulsed Drain Current ①	38		36		Amps
V _{GS}	Gate-Source Voltage	±30				Volts
P _D	Total Power Dissipation @ T _C = 25°C, Derate Above 25°C	180				Watts
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 to 150				°C

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number		MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250 \mu A$)	APT5085BN / APT501R1BN	500			Volts
		APT4585BN / APT451R1BN	450			Volts
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)				250	μA
	($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)				1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)				± 100	nA
$I_{D(ON)}$	On State Drain Current ^② ($V_{DS} > I_{D(ON)} \times R_{DS(ON)} \text{ Max}, V_{GS} = 10V$)	APT5085BN / APT4585BN	9.5			Amps
		APT501R1BN / APT451R1BN	9.0			Amps
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 1mA$)		2		4	Volts
$R_{DS(ON)}$	Static Drain-Source On-State Resistance ^② ($V_{GS} = 10V, I_D = 0.5 I_D [\text{Cont.}]$)	APT5085BN / APT4585BN			0.85	Ohms
		APT501R1BN / APT451R1BN			1.10	Ohms

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.68	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction to Ambient			40	$^\circ\text{C/W}$
T_L	Max. Lead Temp. for Soldering Conditions: 0.063" from Case for 10 Sec.			300	$^\circ\text{C}$

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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DYNAMIC CHARACTERISTICS

APT5085/4585/501R1/451R1BN

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1 \text{ MHz}$		740	950	pF
C_{oss}	Output Capacitance			167	234	pF
C_{rss}	Reverse Transfer Capacitance			63	94	pF
Q_g	Total Gate Charge ③	$V_{GS} = 10V, I_D = I_D [Cont.]$ $V_{DD} = 0.5 V_{DSS}$		33	55	nC
Q_{gs}	Gate-Source Charge			5.6	8	nC
Q_{gd}	Gate-Drain ("Miller") Charge			16	24	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [Cont.], V_{GS} = 15V$ $R_G = 1.8\Omega$		10	20	ns
t_r	Rise Time			14	28	ns
$t_{d(off)}$	Turn-off Delay Time			35	48	ns
t_f	Fall Time			11	22	ns

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT5085BN / APT4585BN		9.5	Amps
		APT501R1BN / APT451R1BN		9.0	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)	APT5085BN / APT4585BN		38	Amps
		APT501R1BN / APT451R1BN		36	Amps
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -I_D [Cont.]$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_D [Cont.], dI_S/dt = 100A/\mu s$)	108	216	432	ns
Q_{rr}	Reverse Recovery Charge	1.2	2.5	5.0	μC

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions / Part Number	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	$V_{DS} = 0.4 V_{DSS}, I_{DS} = P_D / 0.4 V_{DSS}, t = 1 \text{ Sec.}$	180			Watts
SOA2	Safe Operating Area	$I_{DS} = I_D [Cont.], V_{DS} = P_D / I_D [Cont.], t = 1 \text{ Sec.}$	180			Watts
I_{LM}	Inductive Current Clamped	APT5085BN / APT4585BN	38			Amps
		APT501R1BN / APT451R1BN	36			Amps

① Repetitive Rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance Curve. (Fig. 1)

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

APT Reserves the right to change, without notice, the specifications and information contained herein.

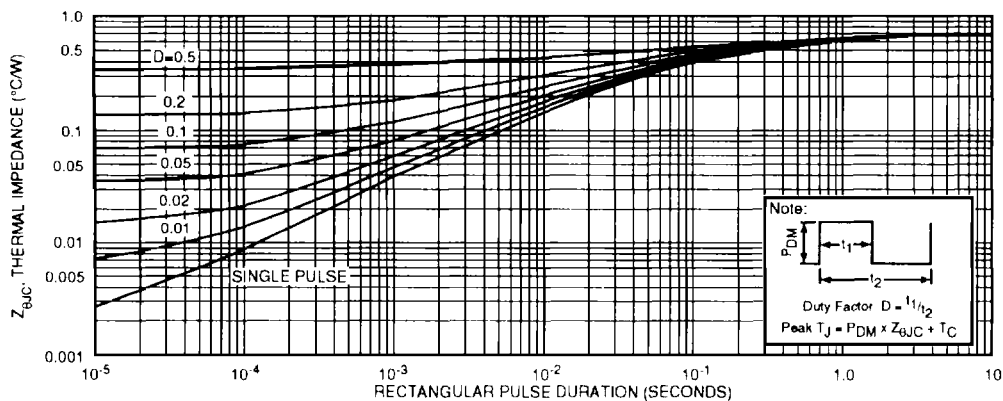
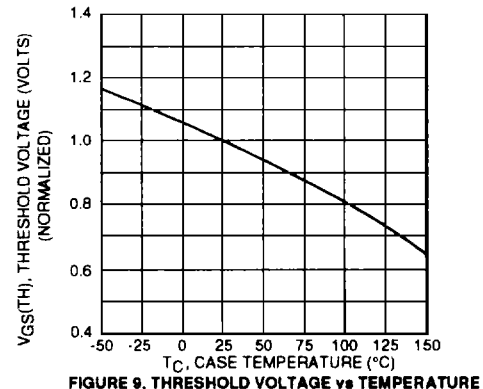
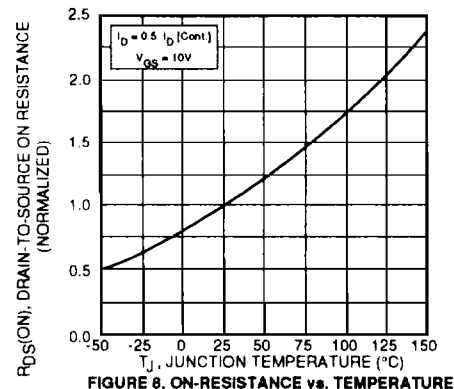
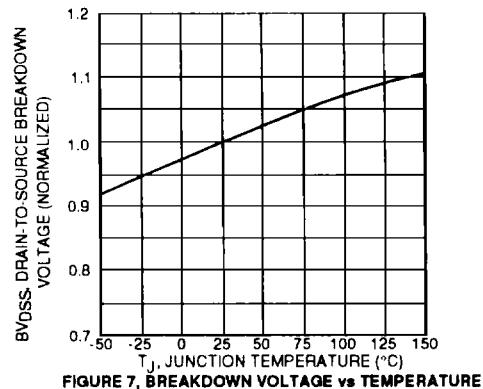
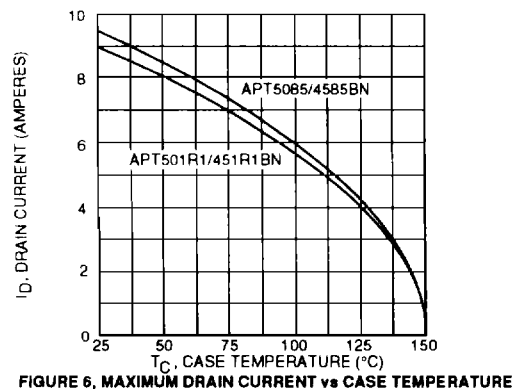
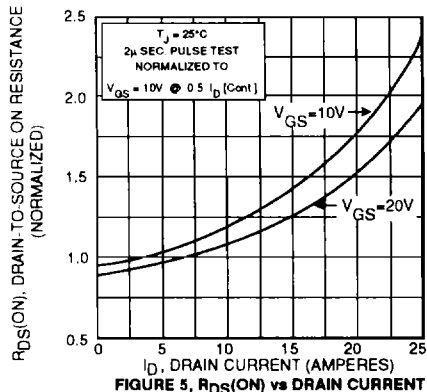
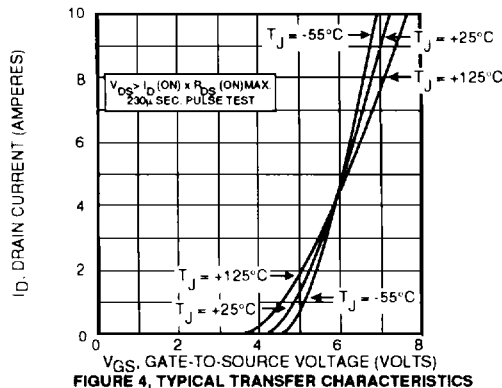
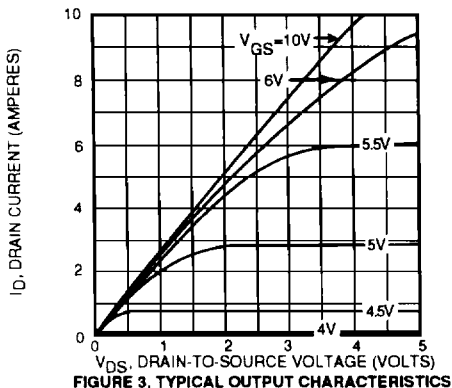
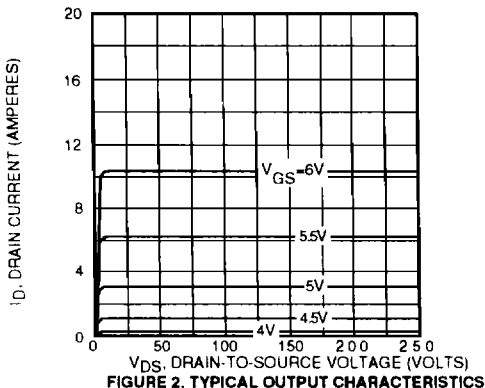
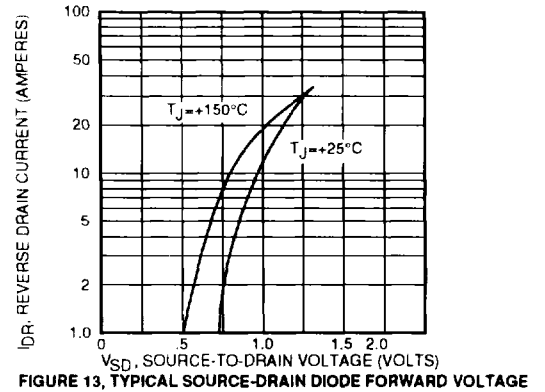
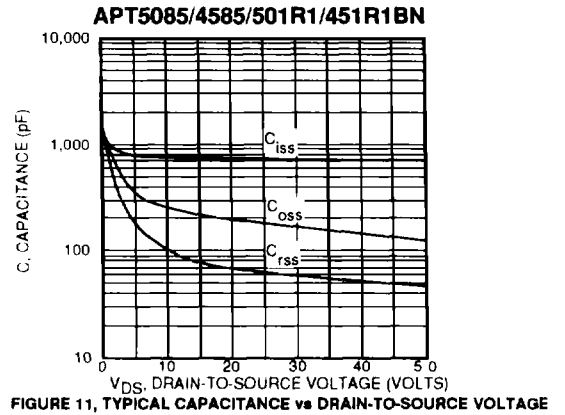
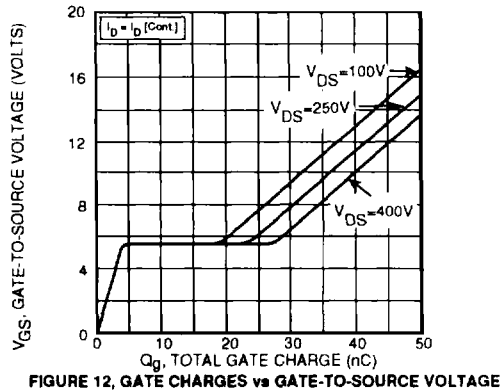
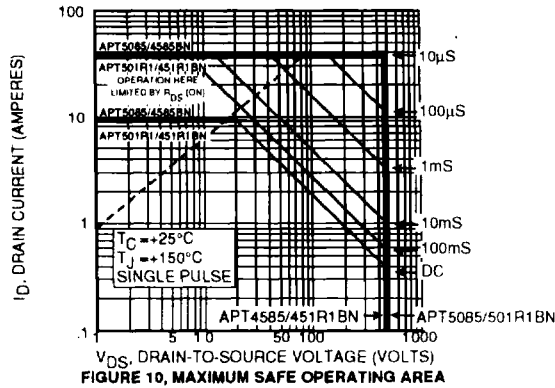


FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

APT5085/4585/501R1/451R1BN





TO-247AD Package Outline

